

Effect of pressure on the correlation gap in a compound with intermediate valency SmB_6

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(Submitted 8 August 1983)

Pis'ma Zh. Eksp. Teor. Fiz. **38**, No. 8, 393–396 (25 October 1983)

It is found that the correlation gap E_g in SmB_6 , which under normal pressure ~ 4 meV, decreases under the action of pressure p and vanishes at $p \approx 55$ kbar. In the pressure range $p > 60$ kbar, the resistance of SmB_6 as a function of temperature $R(T)$ exhibits a metallic behavior, which indicates a pressure-induced transition of samarium in SmB_6 from the state with intermediate valency ν [$\nu(\text{Sm}) = 2.6$ at $p = 0$] to integer valency $\nu = 3$ for $p > 60$ kbar.

PACS numbers: 72.60. + g, 72.80.Jc, 62.50. + p, 71.25.Tn

1. Samarium hexaboride is a samarium compound with fluctuating valency (CFV)¹ with a Fermi level ε_F , intersecting a very narrow $4f$ band with a density of states $g(\varepsilon)$, exceeding approximately 100-fold the density of states in wide bands of normal metals. At $p = 0$, the valence ν of samarium in SmB_6 is 2.66.² Since the compounds of the type R^{2+}B_6 (R is an ion of a rare-earth element) are semiconductors,² and R^{3+}B_6 are analogs of closely valent metals,² one would expect, therefore, that SmB_6 would also be a metal with $g(\varepsilon_F) \neq 0$. However, in reality, SmB_6 is a semiconductor, in which the gap E_g is (2–4) meV, i.e., near ε_F on a background of a relatively high density of states $g(\varepsilon)$, there is an extremely narrow and deep gap (see insert a in Fig. 1).

The reason for the presence of this gap has not yet been completely understood. There are theories relating its presence to the Wigner crystallization,² as well as models³ that examine the interelectronic correlation and CFV, which leads to the appearance of the so-called hybridization gap.

Recently, it was found^{4,5} that the weak semiconducting behavior of $R(T)$ in the “gold” phase of SmS is suppressed at $p \gtrsim 20$ kbar, which is interpreted as a pressure-

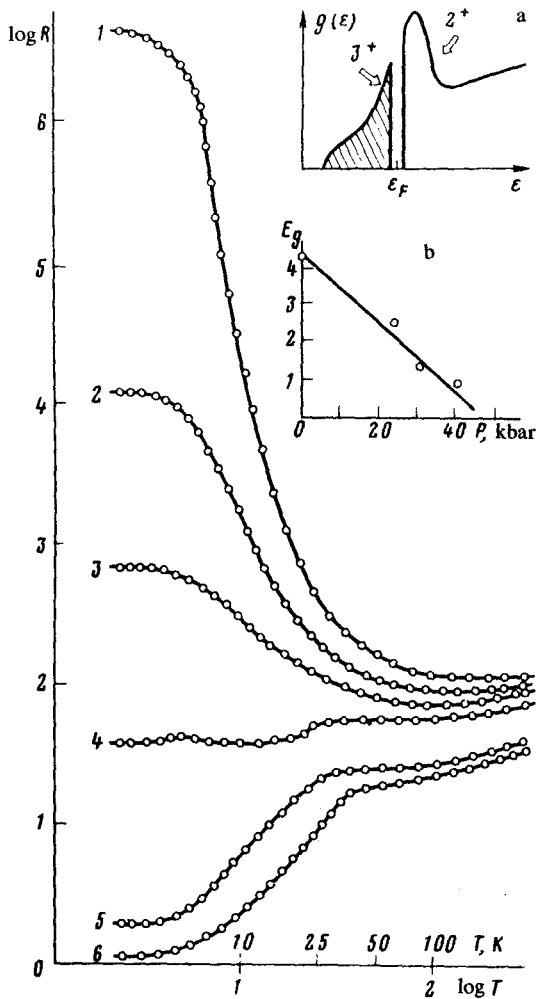


FIG. 1. Temperature dependence of the resistance $R(T)$ in SmB_6 under different pressures (in kbar). 1) 0, 2) 24, 3) 40, 4) 57, 5) 70, and 6) 108. The insert illustrates the behavior of the density of states $g(\epsilon)$ (a) and the dependence of the gap size E_g on the pressure p (b).

induced transition to a trivalent state of Sm in SmS, accompanied by disappearance of the correlation gap near ϵ_F . However, the existence of a gap in SmS in the "gold" phase is not reliably established at the present time.

In contrast to SmS, the presence of a gap near ϵ_F in SmB_6 is confirmed by different methods⁶⁻⁸ and does not give rise to any doubts. In this connection, it was of interest to investigate the effect of pressure on the temperature and field dependences of the resistance R in single-crystalline specimens of SmB_6 .

2. The measurements were performed under pressure up to 110 kbar in magnetic fields up to 50 kOe in the temperature range 2–300 K. Single crystals of SmB_6 with

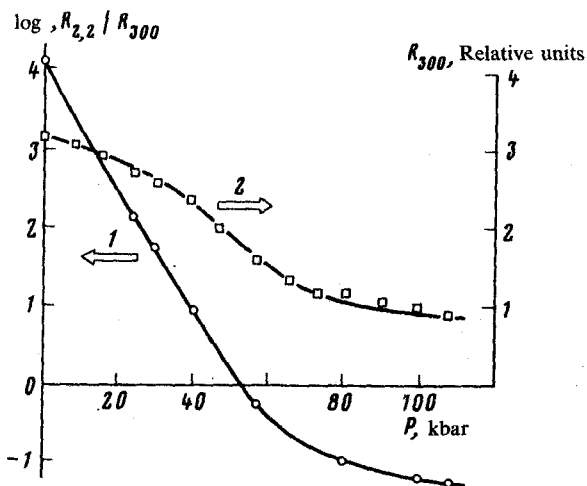


FIG. 2. Pressure dependence of the reduced resistance at low temperatures (1) and the resistance at $T = 300$ K (2).

$T_{\text{melt}} \approx 2800$ K and a resistance ratio of $R(4.2 \text{ K})/R(300 \text{ K}) \approx 2 \times 10^4$ were grown at the Institute of Problems in Material Engineering of the Ukrainian Academy of Sciences (Kiev).

3. Under the action of pressure, the resistance ratio $R(2.2 \text{ K})/R(300 \text{ K})$ decreases (see Fig. 2, curve 1). The size of the gap E_g , determined from the slope of the linear sections of the dependences $\log R = f(1/T)$, decreases simultaneously. At $p \approx 55$ kbar, E_g vanishes (see insert b in Fig. 1). At $p > 55$ kbar, the dependence $R(T)$ becomes metallic (curves 4, 5, and 6 in Fig. 1). The characteristic feature of curves 4–6 is the presence of a distinct inflection in the temperature region 4–40 K. Above this region, R is a weakly linear function of T . The ratio $R(p=0)/R(p=108 \text{ kbar})$ at $T = 300$ K is equal to 4 and increases to 2.5×10^6 when T decreases to 2.2 K.

It is interesting to note that at $p = 57$ kbar (curve 4 in Fig. 1), the decrease in R with a decrease in temperature in the range $10 < T < 300$ K as 10 K is approached is replaced by a Kondo increase (see curve 1 in Fig. 3). Then, with further cooling, in the temperature range 3.5–3 K, the resistance decreases abruptly by 4%.

At pressures up to 40 kbar, the magnetoresistance is negative $\Delta R(H)/R_0 = 4.7 \times 10^{-6} H^2$, and at pressures exceeding 60 kbar, it is positive: $\Delta R(H)/R_0 = 6.8 \times 10^{-6} H^2$ (H is in kilo-oersteds).

4. A change in the temperature dependence of R as a function of T under pressure (Fig. 1) can be interpreted as follows. Since at $p = 0$ the valence of Sm in SmB_6 is $\nu = 2.66$, the $4f$ level is less than half filled: filled states correspond to $\nu(\text{Sm}) = 2$ with the magnetic moment $\mu = 0$; unfilled states correspond to $\nu(\text{SM}) = 3$ with $\mu \neq 0$. By analogy with the "gold" phase of $\text{SmS}^{4,5}$ and TmSe^9 , it may be conjectured that in SmB_6 the $4f$ level is also displaced under pressure upwards relative to ϵ_F . It is then logical to attribute a decrease in E_g (insert b in Fig. 1), on the one hand, to a decrease

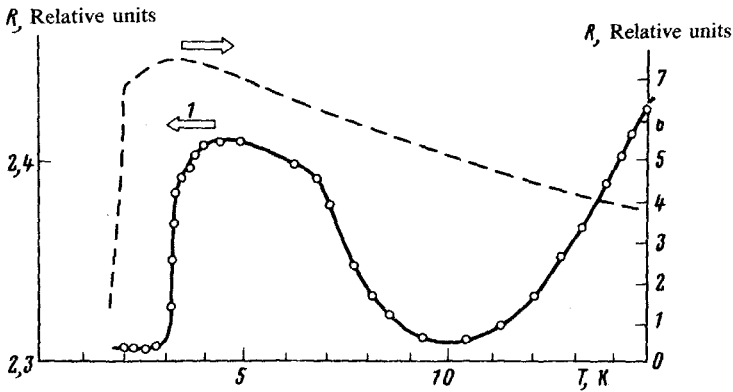


FIG. 3. Temperature dependence of the resistance in SmB_6 and in CeB_6 at $p = 0$ (2).

in the density $g_{4f}(\epsilon_F)$ of the $4f$ states and, on the other hand, to an increase in the degree of f - d hybridization, since in SmB_6 the number of electrons in the d band is equal to the number of states of Sm^{3+} in the $4f$ band, which increases with increasing pressure (insert a in Fig. 1). Both the decrease in $g_{4f}(\epsilon_F)$ and the intensification of hybridization lead to a decrease in the interelectronic correlations, which must lead to a decrease in E_g .

At $p \approx 60$ kbar, the shape of the curves $R(T)$ is analogous to the dependences of R on T for $\text{CeAl}_2(T > 4 \text{ K})$ ¹⁰ and CeSn_3 ,¹¹ for which the region of the inflection is related to the splitting of the magnetic states of Ce^{3+} in a crystal field. From this point of view, the metallic behavior of $R(T)$ in SmB_6 and the change in sign of the magnetoresistance at $p \approx 55$ kbar could correspond to a transition to the trivalent state of Sm in SmB_6 , when SmB_6 turns out to be the analog of a univalent metal. However, the possibility that metallic behavior of the resistance $R(T)$ also appears in the phase with the intermediate valency, when the valence of Sm is close to 3, but is not yet an integer, has not been ruled out.

We note that, in contrast to CFV with Ce and Eu, in which the states with the highest valence of the rare-earth metal are nonmagnetic (in Ce^{3+} , $J = 5/2$ and in Ce^{4+} , $J = 0$), in CFV with Sm the opposite occurs: in Sm^{2+} , $J = 0$, while in Sm^{3+} , $J = 5/2$. As a result of this, the increase in the valency of Sm in CFV does not lead to a decrease in the density of magnetic centers (as for Ce and Eu), but to an increase in this density.

If we assume that at a pressure 57 kbar, the valence of Sm ions in SmB_6 is equal to 3, while $J = 5/2$, then at this pressure, SmB_6 is a unique analog of CeB_6 , in which the Ce ions are trivalent and have $J = 5/2$.

We can assume in this case that the jump in the resistance in SmB_6 at $p = 57$ kbar and $T = 3.4 \text{ K}$ (curve 1 in Fig. 3) has the same nature as in CeB_6 at $p = 0$ and $T = 3.2 \text{ K}$ (curve 2 in Fig. 3), i.e., it is a result of a transition to the antiferromagnetic state. The absence of an analogous transition in SmB_6 at high pressures (curves 5 and 6 in Fig. 1) is apparently explained by the pressure-induced decrease in the transition temperature.

Thus SmB_6 , a semiconducting CFV with a correlation gap in ϵ_F , just as SmS and TmSe , goes over under compression to a metallic state.

In conclusion, we take the opportunity to thank D. I. Khomskii for a discussion of the results.

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Translated by M. E. Alferieff

Edited by S. J. Amoretty